

# Transport Properties of Low-noise of La - Ca - Sr - Mn - O bulks with High Temperature Coefficient of Resistance

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## ABSTRACT

In this article, we study the doping effect on the values of temperature coefficient of resistance (TCR) and metal-insulator transition temperature (TP) of La-Ca-Sr-Mn-O bulks. We found that the maximum values of TCR (TCRMAX) was decreased for  $\text{La}_{0.75}\text{Ca}_{0.25-x}\text{Sr}_x\text{MnO}_3$  with an increased  $x$ , accompanying with an increase of TP. We also study the effect of atomic ratio of O/Mn on TCRMAX and TP for the  $\text{La}_{0.75}\text{Ca}_{0.15}\text{Sr}_{0.1}\text{MnO}_3$  sample. We find that for the sample annealed at 1000 °C, the value of the O/Mn ratio becomes to be 4.1, and the value of TP is increased to 316 K, accompanying an increased TCRMAX value of 9.81 %/K.

In addition, the relationship between TCRMAX and bipolaron binding energy ( $E_b$ ) is deduced by the current-carries-density-collapse model. It is found that the TCRMAX increases as  $E_b$  is decreased, being consistent with the theoretic prediction.

Finally, the noise spectra for the  $\text{La}_{0.75}\text{Ca}_{0.25-x}\text{Sr}_x\text{MnO}_3$  sample were measured with a home made Low-noise amplifier. It is found that value of noise is below  $1.2 \times 10^{-9}$  Hz<sup>-0.5</sup>

Keywords : infrared detectors、 temperature coefficient of resistance(TCR)、 metal-insulator transition temperature(TP)、 current-carries-density-collapse、 bipolaron、 Johnson noise

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